

PSMN3R5-80ES

N-channel 80 V, 3.5 m Ω standard level MOSFET in I2PAK Rev. 02 — 19 April 2011 Product data

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in I2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switch

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	80	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1]	-	-	120	Α
P _{tot}	total power dissipation	$T_{mb} = 25 ^{\circ}\text{C}$; see Figure 2		-	-	338	W
Tj	junction temperature			-55	-	175	°C
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{}$		-	5	5.8	mΩ
		$V_{GS} = 10 \text{ V; } I_{D} = 25 \text{ A;}$ $T_{j} = 25 \text{ °C; see } \frac{\text{Figure } 13}{\text{ Figure } 13}$	[2]	- 3	3	3.5	mΩ
Dynamic ch	naracteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 75 \text{ A};$		-	27	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 40 V; see <u>Figure 14</u> ; see <u>Figure 15</u>		-	139	-	nC
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; V_{sup} ≤ 80 V; R_{GS} = 50 Ω; unclamped		-	-	676	mJ



- [1] Continuous current is limited by package.
- [2] Measured 3 mm from package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		G (EA)
mb	D	drain		
				mbb076 Ś
			∐ ∐ 1 2 3	
			SOT226 (I2PAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN3R5-80ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

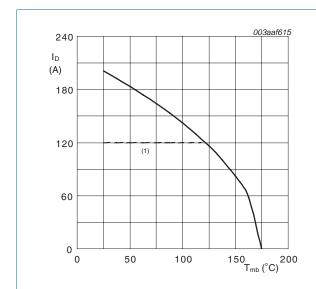
Limiting values

Limiting values Table 4.

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	80	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	80	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{1}}$	[1]	-	120	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	120	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3		-	803	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	338	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	diode					
Is	source current	T _{mb} = 25 °C	[1]	-	120	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	803	Α
Avalanche ru	ggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; V_{sup} ≤ 80 V; R_{GS} = 50 Ω ; unclamped		-	676	mJ

[1] Continuous current is limited by package.



 $V_{GS} \ge 10 \text{ V}$; (1) capped at 120 A due to package.

Continuous drain current as a function of mounting base temperature

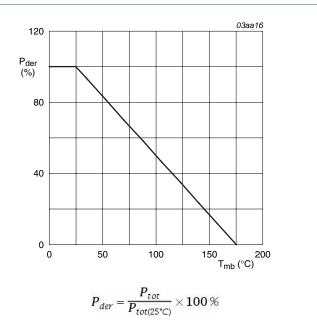


Fig 2. Normalized total power dissipation as a function of mounting base temperature

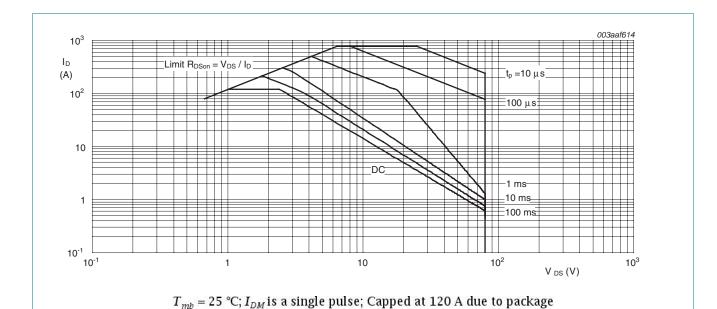
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Fig 3.

N-channel 80 V, 3.5 m Ω standard level MOSFET in I2PAK



Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.44	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W

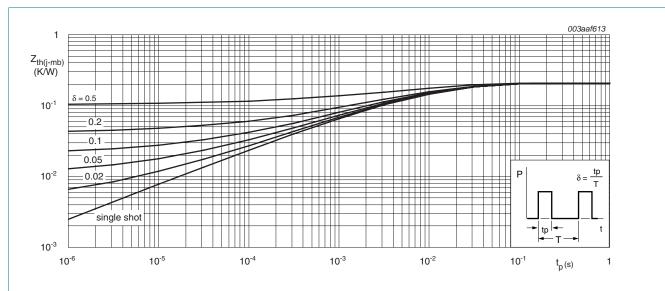


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	73	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 10	1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; see Figure 10	-	-	4.6	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	10	μΑ
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R _{DSon} drain-source on-state resistance		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12	-	7.2	8.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	5	5.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13	[1] -	3	3.5	mΩ
R_G	internal gate resistance (AC)	f = 1 MHz	-	0.9	-	Ω
Dynamic (characteristics					
Q _{G(tot)} total gate charge		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	135	-	nC
		$I_D = 75 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	139	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	51	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	30	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	21	-	nC
Q _{GD}	gate-drain charge		-	27	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}$; $V_{DS} = 40 \text{ V}$; see Figure 14; see Figure 15	-	5.8	-	V
C _{iss}	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	9961	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	847	-	pF
C _{rss}	reverse transfer capacitance		-	401	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 0.53 \Omega;$	-	41	-	ns
t _r	rise time	V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω ; I_D = 75 A	-	43	-	ns
t _{d(off)}	turn-off delay time		-	109	-	ns
t _f	fall time		-	44	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain	n diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$;	-	63	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$	-	121	-	nC

[1] Measured 3 mm from package.

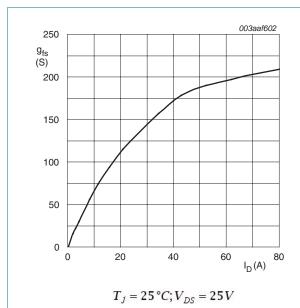


Fig 5. Forward transconductance as a function of drain current; typical values

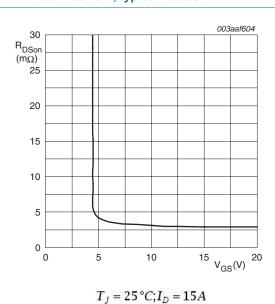
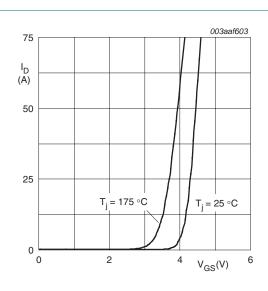
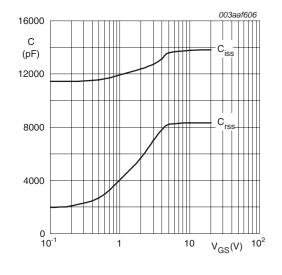


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $V_{DS} = 0V; f = 1MHz$

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

PSMN3R5-80ES

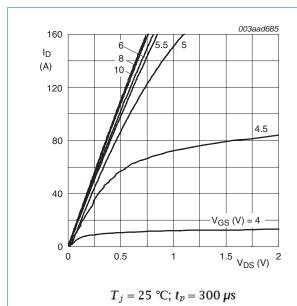


Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values

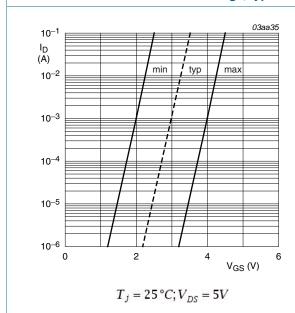


Fig 11. Sub-threshold drain current as a function of gate-source voltage

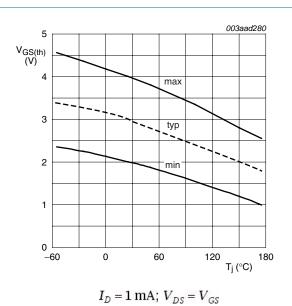


Fig 10. Gate-source threshold voltage as a function of junction temperature

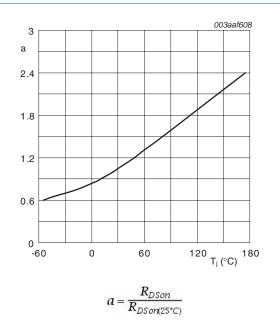
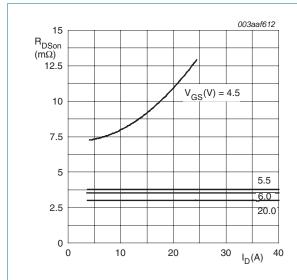


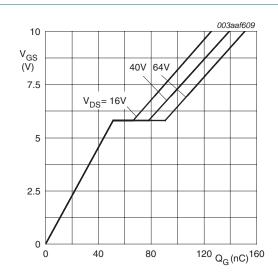
Fig 12. Normailzed drain-source on-state resistance factor as a function of junction temperature

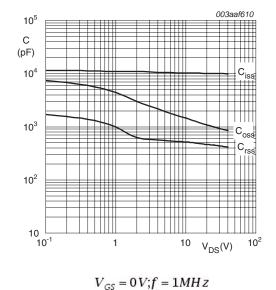


V_{GS}(pl)
V_{GS}(th)
V_{GS}
Q_{GS1} Q_{GS2}
Q_G(tot)
003aaa508

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

Fig 14. Gate charge waveform definitions

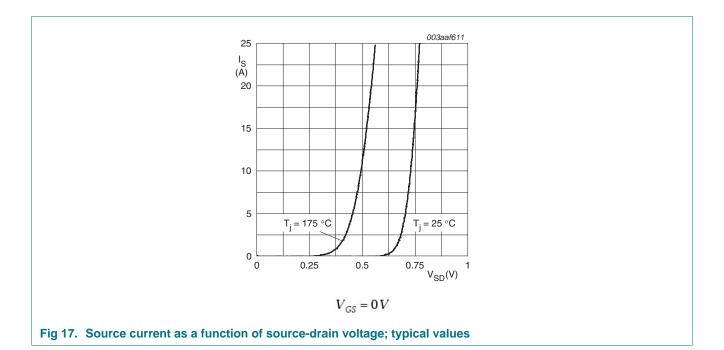




 $T_j = 25$ °C; $I_D = 75$ A

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

Fig 15. Gate-source voltage as a function of gate charge; typical values



7. Package outline

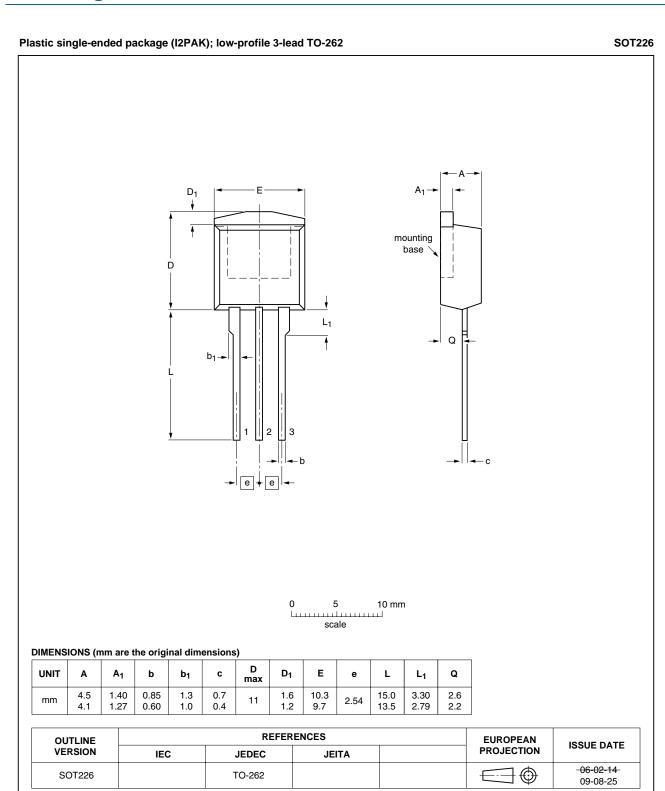


Fig 18. Package outline SOT226 (I2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R5-80ES v.2	20110419	Product data sheet	-	PSMN3R5-80ES v.1
Modifications:	Status changedVarious changes	from objective to product. s to content.		
PSMN3R5-80ES v.1	20101224	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information
4	Limiting values3
5	Thermal characteristics5
6	Characteristics6
7	Package outline
8	Revision history12
9	Legal information13
9.1	Data sheet status
9.2	Definitions13
9.3	Disclaimers
9.4	Trademarks14
10	Contact information